TO-3P

Schottky Barrier Diode in a TO-3P Plastic Package.

Low forward voltage drop, low power losses, High efficiency operation.

OR-ing DC-DC

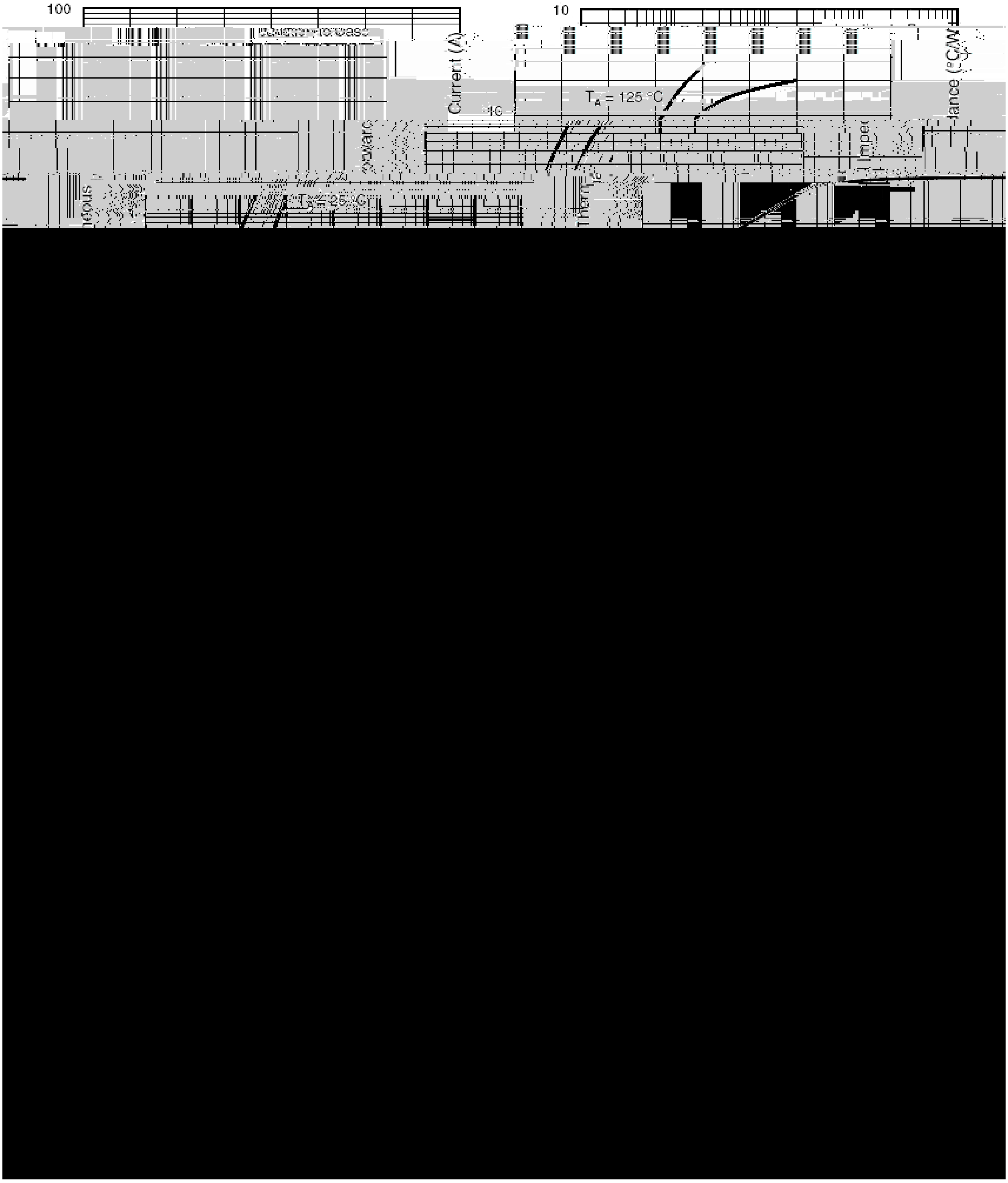
For use in high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

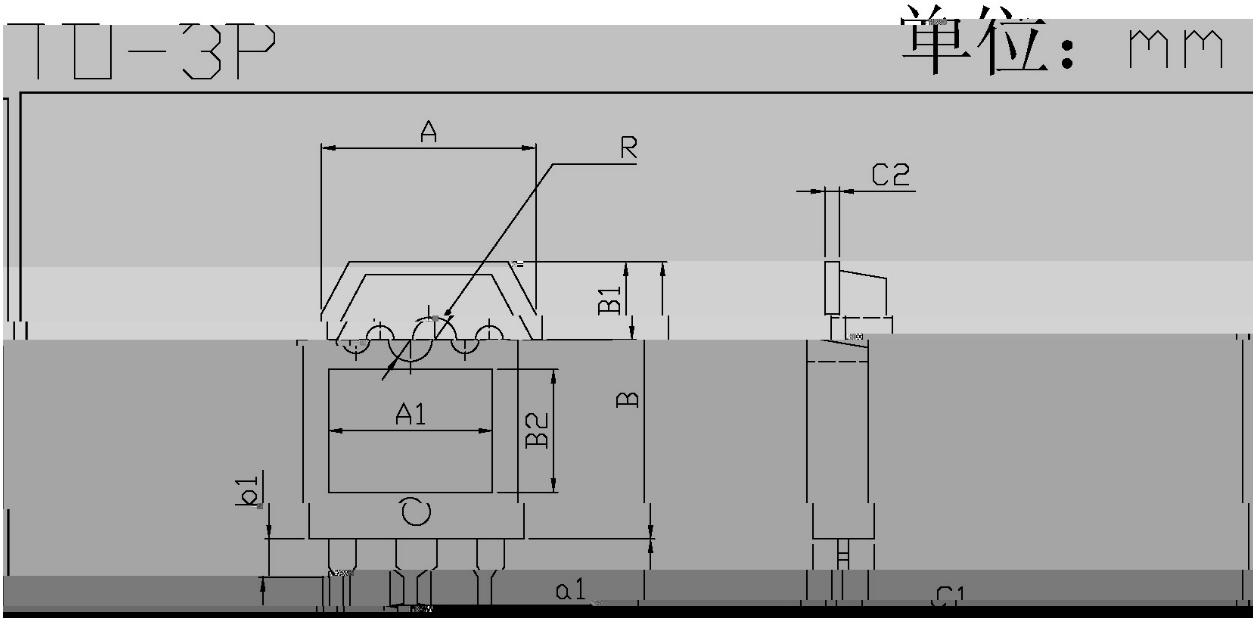
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RWM} V_{DC}	200	V
RMS Reverse Voltage	V_{RMS}	140	V
Average forward current	$I_{F(AV)}$	2 × 15	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	200	A
Thermal Resistance Junction to Ambient case	$R_{\theta Jc}$	1.4	/W
Operating and Storage Temperature Range	T_j T_{stg}	-40 +150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V_{BR}	I_R=1mA(Ta=25)	200			V
Forward Voltage	V_F	I_F =5A(Ta=25)		0.73	0.85	V
		I_F =10A(Ta=25)		0.80	0.95	V
		I_F =15A(Ta=25)		0.92	1.15	V
		I_F =5A(Ta=125)		0.58		V
		I_F =10A(Ta=125)		0.66		V
		I_F =15A(Ta=125)		0.71	0.85	V
Instantaneous Reverse current (Note 1)	I_R Note 1	V_R=200V(Ta=25)		4	20	μA
		V_R=200V(Ta=125)		5	10	mA

/Notes

1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip.


100
Junction to Case
10
Current (A)
T_A = 125 °C
T_A = 25 °C
ance (°C/W)


TO-3P
单位：mm
A
R
C2
B1
B
A1
B2
b1
a1
C1

1 25 150 60 90sec;
2 255±5 5±0.5sec;
3 2 10 /sec.

Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

270±5 10±1 sec.

Temp.:270±5